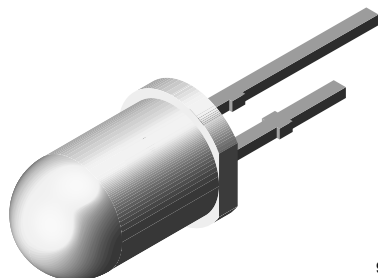




## High Speed Infrared Emitting Diode, 890 nm, Surface Emitter Technology



94 8390

### FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm):  $\varnothing$  5
- Leads with stand-off
- Peak wavelength:  $\lambda_p = 890$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\varphi = \pm 8^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
**GREEN**  
(5-2008)

### DESCRIPTION

TSHF5210 is an infrared, 890 nm emitting diode based on surface emitter chip technology with high radiant power and high speed, molded in a clear, untinted plastic package.

### APPLICATIONS

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK - coded, 450 kHz or 1.3 MHz)

### PRODUCT SUMMARY

| COMPONENT | $I_e$ (mW/sr) | $\varphi$ (°) | $\lambda_p$ (nm) | $t_r$ (ns) |
|-----------|---------------|---------------|------------------|------------|
| TSHF5210  | 327           | $\pm 8$       | 890              | 10         |

#### Note

- Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS                      | PACKAGE FORM      |
|---------------|-----------|------------------------------|-------------------|
| TSHF5210      | Bulk      | MOQ: 4000 pcs, 4000 pcs/bulk | T-1 $\frac{3}{4}$ |

#### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

| PARAMETER                              | TEST CONDITION                          | SYMBOL     | VALUE       | UNIT             |
|--|---|------------|-------------|------------------|
| Reverse voltage                        |   | $V_R$      | 5           | V                |
| Forward current                        |   | $I_F$      | 100         | mA               |
| Peak forward current                   | $t_p/T = 0.5$ , $t_p = 100 \mu\text{s}$ | $I_{FM}$   | 200         | mA               |
| Surge forward current                  | $t_p = 100 \mu\text{s}$                 | $I_{FSM}$  | 1           | A                |
| Power dissipation                      |   | $P_V$      | 170         | mW               |
| Junction temperature                   |   | $T_j$      | 100         | $^\circ\text{C}$ |
| Ambient temperature range              |   | $T_{amb}$  | -40 to +85  | $^\circ\text{C}$ |
| Storage temperature range              |   | $T_{stg}$  | -40 to +100 | $^\circ\text{C}$ |
| Soldering temperature                  | $t \leq 5$ s, 2 mm from case            | $T_{sd}$   | 260         | $^\circ\text{C}$ |
| Thermal resistance junction to ambient | J-STD-051, leads 7 mm, soldered on PCB  | $R_{thJA}$ | 230         | K/W              |

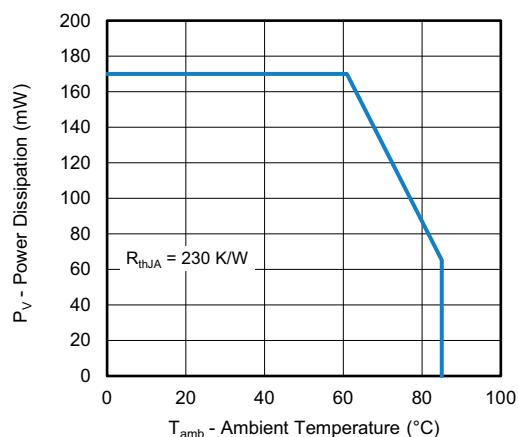


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

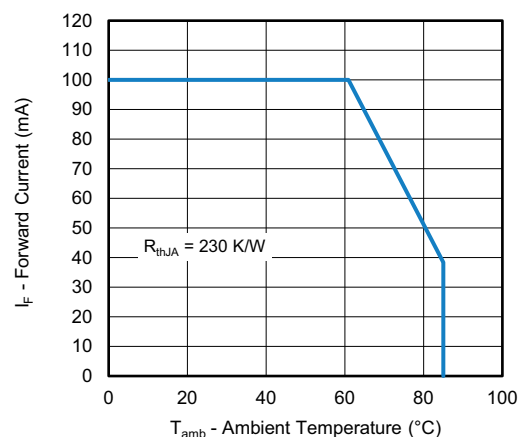


Fig. 2 - Forward Current Limit vs. Ambient Temperature

**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

| PARAMETER                              | TEST CONDITION   | SYMBOL           | MIN.                               | TYP.    | MAX. | UNIT          |
|--|--|------------------|------------------------------------|---------|------|---------------|
| Forward voltage                        | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$                     | $V_F$            | -                                  | 1.5     | 1.7  | V             |
|  | $I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$              | $V_F$            | -                                  | 3       | -    | V             |
| Temperature coefficient of $V_F$       | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$                     | $TK_{VF}$        | -                                  | -1.3    | -    | mV/K          |
| Reverse current                        |  | $I_R$            | Not designed for reverse operation |         |      | $\mu\text{A}$ |
| Junction capacitance                   | $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0\text{ mW/cm}^2$ | $C_j$            | -                                  | 55      | -    | pF            |
| Radiant intensity                      | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$                     | $I_e$            | 150                                | 327     | 450  | mW/sr         |
|  | $I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$              | $I_e$            | -                                  | 2700    | -    | mW/sr         |
| Radiant power                          | $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$                     | $\phi_e$         | -                                  | 53      | -    | mW            |
| Temperature coefficient of $\phi_e$    | $I_F = 100\text{ mA}$  | $TK_{\phi_e}$    | -                                  | -0.3    | -    | %/K           |
| Angle of half intensity                |  | $\phi$           | -                                  | $\pm 8$ | -    | $^{\circ}$    |
| Peak wavelength                        | $I_F = 100\text{ mA}$  | $\lambda_p$      | -                                  | 890     | -    | nm            |
| Spectral bandwidth                     | $I_F = 100\text{ mA}$  | $\Delta\lambda$  | -                                  | 40      | -    | nm            |
| Temperature coefficient of $\lambda_p$ | $I_F = 100\text{ mA}$  | $TK_{\lambda_p}$ | -                                  | 0.3     | -    | nm/K          |
| Rise time                              | $I_F = 100\text{ mA}$  | $t_r$            | -                                  | 10      | -    | ns            |
| Fall time                              | $I_F = 100\text{ mA}$  | $t_f$            | -                                  | 10      | -    | ns            |

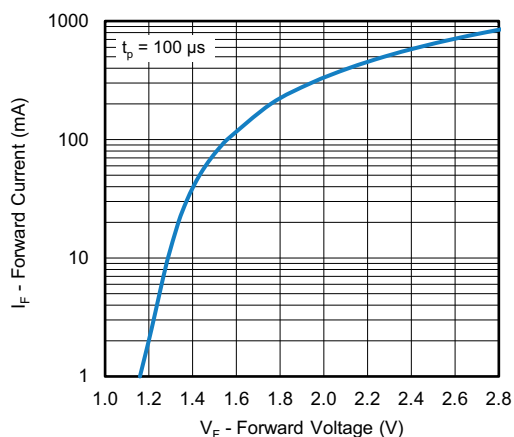
**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

Fig. 3 - Forward Current vs. Forward Voltage

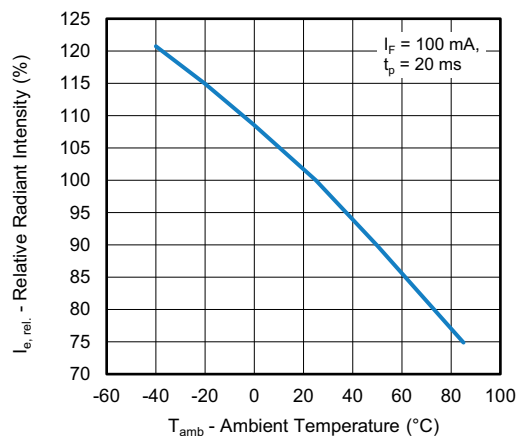


Fig. 6 - Relative Radiant Intensity vs. Ambient Temperature

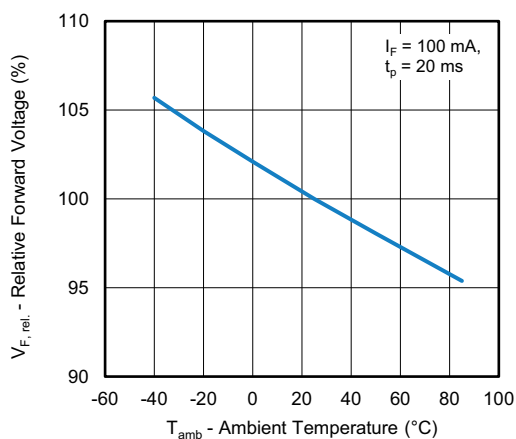


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

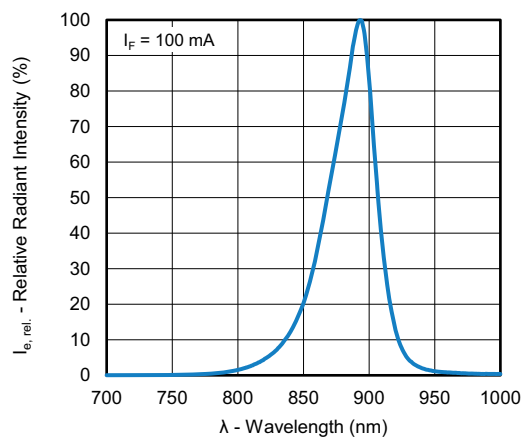


Fig. 7 - Relative Radiant Intensity vs. Wavelength

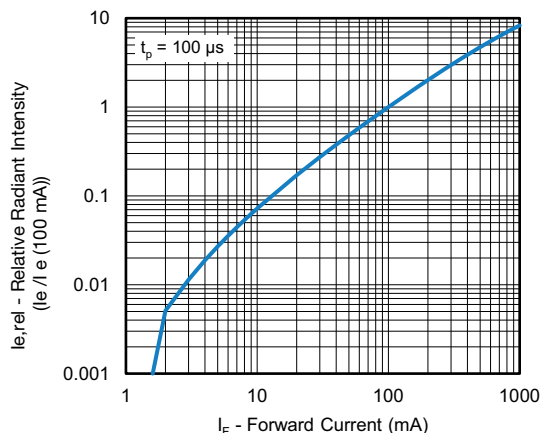


Fig. 5 - Relative Radiant Intensity vs. Forward Current

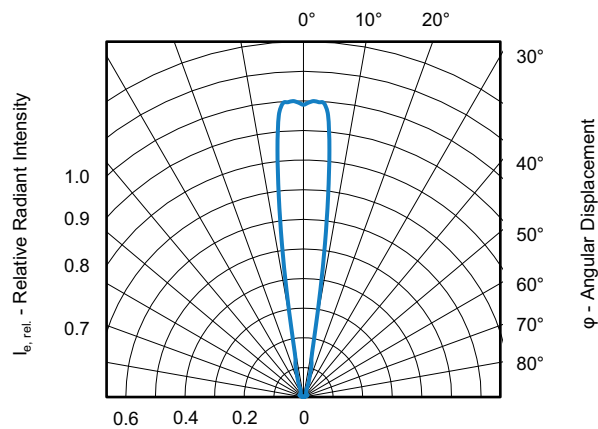
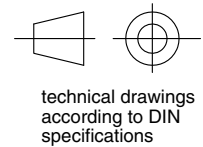
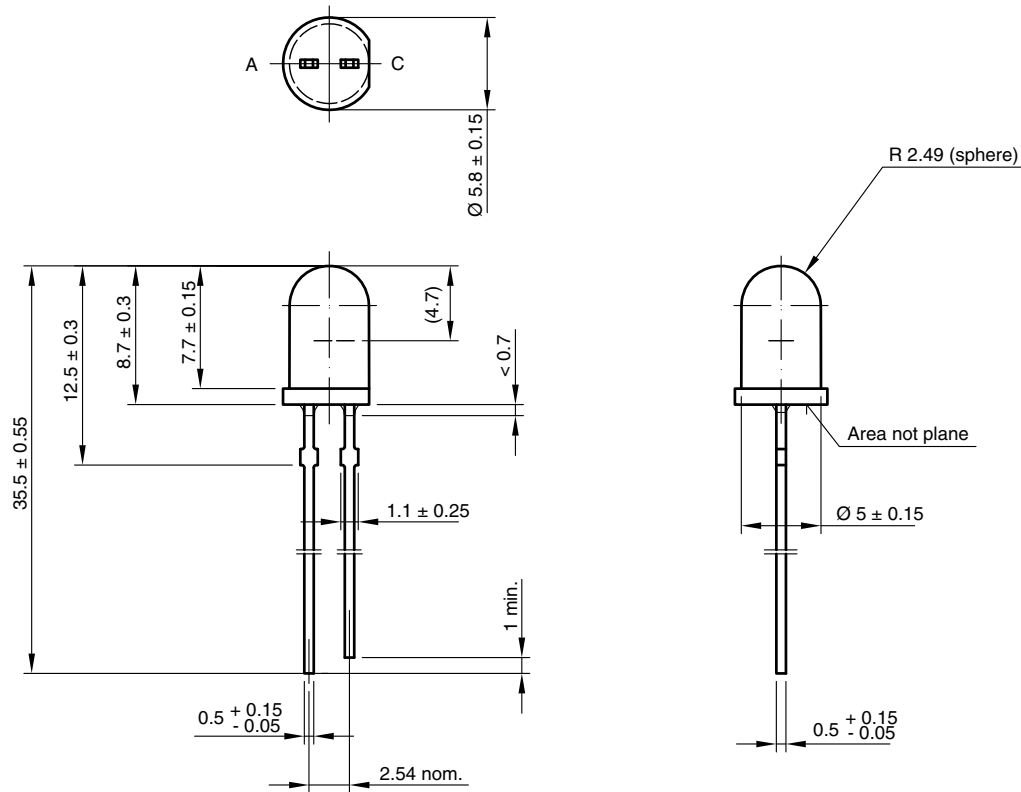


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement



**PACKAGE DIMENSIONS** in millimeters



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